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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I <sup>2</sup> C, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I <sup>2</sup> S, LED, POR, PWM, WDT
Number of I/O	21
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 9x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	PG-VQFN-48-53
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4104q48k128baxuma1

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Data Sheet V1.3, 2015-10



# **Summary of Features**

Table 6 SRAM Memory Ranges

Total SRAM Size	Program SRAM	System Data SRAM
40 Kbytes	1FFF C000 <sub>H</sub> – 1FFF FFFF <sub>H</sub>	2000 0000 <sub>H</sub> – 2000 5FFF <sub>H</sub>
20 Kbytes	1FFF E000 <sub>H</sub> – 1FFF FFFF <sub>H</sub>	2000 0000 <sub>H</sub> – 2000 2FFF <sub>H</sub>

Table 7 ADC Channels<sup>1)</sup>

Package	VADC G0	VADC G1
LQFP-64, TQFP-64	CH0, CH3CH7	CH0, CH1, CH3, CH6
PG-VQFN-48	CH0, CH3CH7	CH0, CH1, CH3

Some pins in a package may be connected to more than one channel. For the detailed mapping see the Port I/O Function table.

# 1.6 Identification Registers

The identification registers allow software to identify the marking.

Table 8 XMC4200 Identification Registers

Register Name	Value	Marking
SCU_IDCHIP	0004 2001 <sub>H</sub>	EES-AA, ES-AA
SCU_IDCHIP	0004 2002 <sub>H</sub>	ES-AB, AB
SCU_IDCHIP	0004 2003 <sub>H</sub>	BA
JTAG IDCODE	101D D083 <sub>H</sub>	EES-AA, ES-AA
JTAG IDCODE	201D D083 <sub>H</sub>	ES-AB, AB
JTAG IDCODE	301D D083 <sub>H</sub>	ВА



#### **General Device Information**

# 2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the different packages.

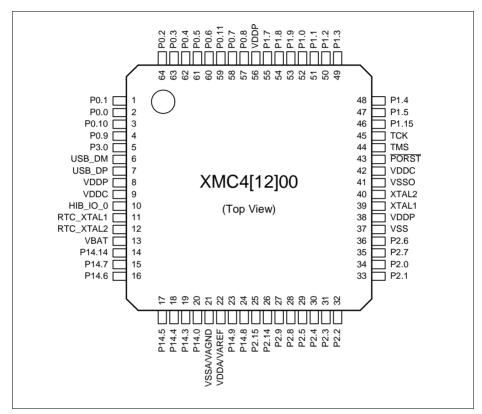


Figure 4 XMC4[12]00 PG-LQFP-64 and PG-TQFP-64 Pin Configuration (top view)



### **General Device Information**

Table 11 Package Pin Mapping (cont'd)

Function	LQFP-64 TQFP-64	VQFN-48	Pad Type	Notes
P14.9	23	19	AN/DAC/DIG_IN	
P14.14	14	-	AN/DIG_IN	
USB_DP	7	4	special	
USB_DM	6	3	special	
HIB_IO_0	B_IO_0 10 7 A1 special		At the first power-up and with every reset of the hibernate domain this pin is configured as open-drain output and drives "0". As output the medium driver mode is active.	
TCK	45	34	A1	Weak pull-down active.
TMS	44	33	A1+	Weak pull-up active. As output the strong-soft driver mode is active.
PORST	43	32	special	Strong pull-down controlled by EVR. Weak pull-up active while strong pull-down is not active.
XTAL1	39	29	clock_IN	
XTAL2	40	30	clock_O	
RTC_XTAL1	11	8	clock_IN	
RTC_XTAL2	12	9	clock_O	
VBAT	13	10	Power	When VDDP is supplied VBAT has to be supplied as well.
VDDA/VAREF	22	18	AN_Power/AN_ Ref	Shared analog supply and reference voltage pin.
VSSA/VAGND	21	17	AN_Power/AN_ Ref	Shared analog supply and reference ground pin.
VDDC	9	6	Power	
VDDC	42	31	Power	
VDDP	8	5	Power	
VDDP	38	28	Power	
VDDP	56	41	Power	
VSS	37	27	Power	



#### **General Device Information**

#### 2.2.2 Port I/O Functions

The following general scheme is used to describe each PORT pin:

Table 12 Port I/O Function Description

Function		Outputs		Inputs				
	ALT1	ALTn	HWO0	HWI0	Input	Input		
P0.0		MODA.OUT	MODB.OUT	MODB.INA	MODC.INA			
Pn.y	MODA.OUT				MODA.INA	MODC.INB		

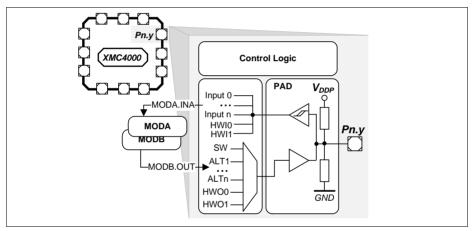


Figure 6 Simplified Port Structure

Pn.y is the port pin name, defining the control and data bits/registers associated with it. As GPIO, the port is under software control. Its input value is read via Pn\_IN.y, Pn\_OUT defines the output value.

Up to four alternate output functions (ALT1/2/3/4) can be mapped to a single port pin, selected by Pn\_IOCR.PC. The output value is directly driven by the respective module, with the pin characteristics controlled by the port registers (within the limits of the connected pad).

The port pin input can be connected to multiple peripherals. Most peripherals have an input multiplexer to select between different possible input sources.

The input path is also active while the pin is configured as output. This allows to feedback an output to on-chip resources without wasting an additional external pin.

By Pn\_HWSEL it is possible to select between different hardware "masters" (HWO0/HWI0). The selected peripheral can take control of the pin(s). Hardware control overrules settings in the respective port pin registers.

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#### **Port I/O Function Table** 2.2.2.1

Table 13	Port I	/O Funct	ions											
Function			Output							Input				
	ALT1	ALT2	ALT3	ALT4	HWO0	HWI0	Input	Input	Input	Input	Input	Input	Input	Input
P0.0		CAN. N0_TXD	CCU80. OUT21	LEDTS0. COL2			U1C1. DX0D		ERU0. 0B0	USB. VBUSDETECT A		HRPWM0. C1INB		
P0.1		U1C1. DOUT0	CCU80. OUT11	LEDTS0. COL3					ERU0. 0A0			HRPWM0. C2INB		
P0.2		U1C1. SELO1	CCU80. OUT01	HRPWM0. HROUT01	U1C0. DOUT3	U1C0. HWIN3			ERU0. 3B3					
P0.3			CCU80. OUT20	HRPWM0. HROUT20	U1C0. DOUT2	U1C0. HWIN2				ERU1. 3B0				
P0.4			CCU80. OUT10	HRPWM0. HROUT21	U1C0. DOUT1	U1C0. HWIN1		U1C0. DX0A	ERU0. 2B3					
P0.5		U1C0. DOUT0	CCU80. OUT00	HRPWM0. HROUT00	U1C0. DOUT0	U1C0. HWIN0		U1C0. DX0B		ERU1. 3A0				
P0.6		U1C0. SELO0	CCU80. OUT30	HRPWM0. HROUT30				U1C0. DX2A	ERU0. 3B2		CCU80. IN2B			
P0.7	WWDT. SERVICE_OUT	U0C0. SELO0		HRPWM0. HROUT11		DB. TDI	U0C0. DX2B		ERU0. 2B1		CCU80. IN0A	CCU80. IN1A	CCU80. IN2A	CCU80. IN3A
P0.8	SCU. EXTCLK	U0C0. SCLKOUT		HRPWM0. HROUT10		DB. TRST	U0C0. DX1B		ERU0. 2A1		CCU80. IN1B			
P0.9	HRPWM0. HROUT31	U1C1. SELO0	CCU80. OUT12	LEDTS0. COL0			U1C1. DX2A		ERU0. 1B0					
P0.10		U1C1. SCLKOUT	CCU80. OUT02	LEDTS0. COL1			U1C1. DX1A		ERU0. 1A0					
P0.11		U1C0. SCLKOUT	CCU80. OUT31					U1C0. DX1A	ERU0. 3A2					
P1.0		U0C0. SELO0	CCU40. OUT3	ERU1. PDOUT3			U0C0. DX2A		ERU0. 3B0		CCU40. IN3A	HRPWM0. COINA		
P1.1		U0C0. SCLKOUT	CCU40. OUT2	ERU1. PDOUT2			U0C0. DX1A	POSIF0. IN2A	ERU0. 3A0		CCU40. IN2A	HRPWM0. C1INA		
P1.2			CCU40. OUT1	ERU1. PDOUT1	U0C0. DOUT3	U0C0. HWIN3		POSIF0. IN1A		ERU1. 2B0	CCU40. IN1A	HRPWM0. C2INA		
P1.3		U0C0. MCLKOUT	CCU40. OUT0	ERU1. PDOUT0	U0C0. DOUT2	U0C0. HWIN2		POSIFO. INOA		ERU1. 2A0	CCU40. INOA	HRPWM0. COINB		
P1.4	WWDT. SERVICE_OUT	CAN. NO_TXD	CCU80. OUT33		U0C0. DOUT1	U0C0. HWIN1	U0C0. DX0B	CAN. N1_RXDD	ERU0. 2B0		CCU41. INOC	HRPWM0. BL0A		
P1.5	CAN. N1_TXD	U0C0. DOUT0	CCU80. OUT23		U0C0. DOUT0	U0C0. HWIN0	U0C0. DX0A	CAN. NO_RXDA	ERU0. 2A0	ERU1. 0A0	CCU41. IN1C			
P1.7		U0C0. DOUT0		U1C1. SELO2						USB. VBUSDETECT B				



XMC4000 Family



Table 13 Port I/O Functions (CONt'd)

Function			Output			Input								
	ALT1	ALT2	ALT3	ALT4	HWO0	HWI0	Input	Input	Input	Input	Input	Input	Input	Input
P14.9					DAC. OUT_1			VADC. G1CH1						
P14.14								VADC. G1CH6					G1ORC6	
USB_DP														
USB_DM														
HIB_IO_0	HIBOUT	WWDT. SERVICE_OUT					WAKEUPA			USB. VBUSDETECT C				
тск						DB.TCK/ SWCLK								
TMS					DB.TMS/ SWDIO									
PORST														
XTAL1							U0C0. DX0F	U0C1. DX0F	U1C0. DX0F	U1C1. DX0F				
XTAL2														
RTC_XTAL1									ERU0. 1B1					
RTC_XTAL2														



The XMC4[12]00 has a common ground concept, all  $V_{\rm SS}$ ,  $V_{\rm SSA}$  and  $V_{\rm SSO}$  pins share the same ground potential. In packages with an exposed die pad it must be connected to the common ground as well.

There are no dedicated connections for the analog reference  $V_{\rm AREF}$  and  $V_{\rm AGND}$ . Instead, they share the same pins as the analog supply pins  $V_{\rm DDA}$  and  $V_{\rm SSA}$ . Some analog channels can optionally serve as "Alternate Reference"; further details on this operating mode are described in the Reference Manual.

When  $V_{\rm DDP}$  is supplied,  $V_{\rm BAT}$  must be supplied as well. If no other supply source (e.g. battery) is connected to  $V_{\rm BAT}$ , the  $V_{\rm BAT}$  pin can also be connected directly to  $V_{\rm DDP}$ .



# 3.1.5 Operating Conditions

The following operating conditions must not be exceeded in order to ensure correct operation and reliability of the XMC4[12]00. All parameters specified in the following tables refer to these operating conditions, unless noted otherwise.

Table 20 Operating Conditions Parameters

Parameter	Symbol		Values	1	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Ambient Temperature	$T_{A}$ SR	-40	_	85	°C	Temp. Range F
		-40	_	125	°C	Temp. Range K
Digital supply voltage	$V_{\mathrm{DDP}}\mathrm{SR}$	3.13 <sup>1)</sup>	3.3	3.63 <sup>2)</sup>	V	
Core Supply Voltage	$V_{ m DDC}$	_1)	1.3	_	V	Generated internally
Digital ground voltage	$V_{\mathrm{SS}}$ SR	0	_	_	٧	
ADC analog supply voltage	$V_{DDA}SR$	3.0	3.3	3.6 <sup>2)</sup>	V	
$ \overline{ \text{Analog ground voltage for} } \\ V_{\text{DDA}} $	$V_{SSA}SR$	-0.1	0	0.1	V	
Battery Supply Voltage for Hibernate Domain <sup>3)</sup>	$V_{BAT}SR$	1.95 <sup>4)</sup>	_	3.63	V	When $V_{\rm DDP}$ is supplied $V_{\rm BAT}$ has to be supplied as well.
System Frequency	$f_{\mathrm{SYS}}$ SR	_	_	80	MHz	
Short circuit current of digital outputs	I <sub>SC</sub> SR	-5	_	5	mA	
Absolute sum of short circuit currents per pin group <sup>5)</sup>	$\Sigma I_{\mathrm{SC\_PG}}$ SR	_	_	20	mA	
Absolute sum of short circuit currents of the device	$\Sigma I_{\text{SC\_D}}$ SR	-	-	100	mA	

<sup>1)</sup> See also the Supply Monitoring thresholds, Section 3.3.2.

<sup>2)</sup> Voltage overshoot to 4.0 V is permissible at Power-Up and PORST low, provided the pulse duration is less than 100 μs and the cumulated sum of the pulses does not exceed 1 h over lifetime.

<sup>3)</sup> Different limits apply for LPAC operation, Section 3.2.6

<sup>4)</sup> To start the hibernate domain it is required that V<sub>BAT</sub> ≥ 2.1 V, for a reliable start of the oscillation of RTC\_XTAL in crystal mode it is required that V<sub>BAT</sub> ≥ 3.0 V.

<sup>5)</sup> The port groups are defined in Table 18.



Table 24 HIB\_IO Class\_A1 special Pads

Parameter	Symbol	Va	lues	Unit	Note /	
		Min.	Max.		Test Condition	
Input leakage current	$I_{OZHIB}$ CC	-500	500	nA	$0 \text{ V} \leq V_{IN} \leq V_{BAT}$	
Input high voltage	$V_{\mathrm{IHHIB}}$ SR	$0.6  imes V_{BAT}$	$V_{BAT}$ + 0.3	V	max. 3.6 V	
Input low voltage	$V_{ILHIB}$ SR	-0.3	$0.36  imes V_{BAT}$	V		
Input Hysteresis for	HYSHIB	$0.1  imes V_{BAT}$	_	V	$V_{BAT} \geq 3.13\;V$	
HIB_IO pins <sup>1)</sup>	CC	$0.06  imes V_{BAT}$	-	V	$V_{\mathrm{BAT}}$ < 3.13 V	
Output high voltage, POD <sup>1)</sup> = medium	$V_{OHHIB}$ CC	V <sub>BAT</sub> - 0.4	_	٧	$I_{\mathrm{OH}} \geq$ -1.4 mA	
Output low voltage	$V_{OLHIB}$ CC	-	0.4	V	$I_{\rm OL} \le 2 \; {\rm mA}$	
Fall time	t <sub>FHIB</sub> CC	-	50	ns	$V_{\rm BAT} \ge 3.13 \text{ V}$ $C_{\rm L} = 50 \text{ pF}$	
		_	100	ns	$V_{\mathrm{BAT}}$ < 3.13 V $C_{\mathrm{L}}$ = 50 pF	
Rise time	$t_{RHIB}CC$	_	50	ns	$V_{\mathrm{BAT}} \ge 3.13 \ \mathrm{V}$ $C_{\mathrm{L}} = 50 \ \mathrm{pF}$	
		-	100	ns	$V_{\mathrm{BAT}}$ < 3.13 V $C_{\mathrm{L}}$ = 50 pF	

<sup>1)</sup> Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.



 Table 30
 CMP and 10-bit DAC characteristics (Operating Conditions apply)

Parameter	Symbol		Values	3	Unit	Note /
		Min.	Тур.	Max.		Test Condition
CSG Output Jitter	$D_{ extsf{CSG}}$	_	-	1	clk	
Bias startup time	t <sub>start</sub> CC	_	_	98	us	
Bias supply current	I <sub>DDbias</sub> CC	_	_	400	μА	
CSGy startup time	t <sub>CSGS</sub>	_	_	2	μS	
Input operation current <sup>1)</sup>	$I_{ m DDCIN}$	-10	_	33	μА	See Figure 19
High Speed Mode				•	•	
DAC output voltage range	$V_{DOUT}$ CC	$V_{ m SS}$	_	$V_{DDP}$	V	
DAC propagation delay - Full scale	t <sub>FShs</sub> CC	_	_	80	ns	See Figure 20
Input Selector propagation delay - Full scale	t <sub>Dhs</sub> CC	_	_	100	ns	See Figure 20
Comparator bandwidth	t <sub>Dhs</sub> CC	20	-	_	ns	
DAC CLK frequency	$f_{\rm clk}$ SR	_	_	30	MHz	
Supply current	I <sub>DDhs</sub>	_	_	940	μА	
Low Speed Mode						
DAC output voltage range	$V_{DOUT}$ CC	$0.1 \times V_{\text{DDP}}^{2)}$	_	$V_{DDP}$	V	
DAC propagation delay - Full Scale	t <sub>FSIs</sub> CC	_	_	160	ns	See Figure 20
Input Selector propagation delay - Full Scale	t <sub>DIs</sub> CC	_	-	200	ns	See Figure 20
Comparator bandwidth	t <sub>Dls</sub> CC	20	_	_	ns	
DAC CLK frequency	$f_{\rm clk}$ SR	_	_	30	MHz	
Supply current	I <sub>DDIs</sub> CC	_	-	300	μΑ	

<sup>1)</sup> Typical input resistance  $R_{CIN} = 100 \text{kOhm}$ .

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<sup>2)</sup> The INL error increases for DAC output voltages below this limit.



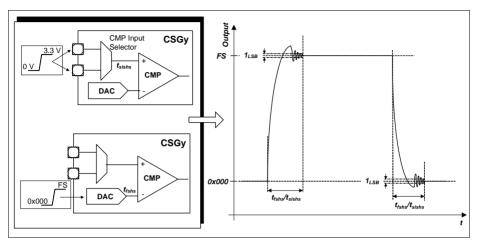


Figure 20 DAC and Input Selector Propagation Delay

#### 3.2.5.3 Clocks

#### **HRPWM DAC Conversion Clock**

The DAC conversion clock can be generated internally or it can be controlled via a HRPWM module pin.

Table 31 External DAC conversion trigger operating conditions

		• •		•		
Parameter	Symbol	,	/alues	Unit	Note /	
		Min.	Тур.	Max.		Test Con dition
Frequency	$f_{ m etrg}$ SR	_	-	30 <sup>2)</sup>	MHz	
ON time	t <sub>onetrg</sub> SR	$2T_{\rm ccu}^{-1)2)}$	-	-	ns	
OFF time	t <sub>offetrg</sub> SR	$2T_{\rm ccu}^{-1)2)}$	-	-	ns	

<sup>1) 50%</sup> duty cycle is not obligatory

#### **CSG External Clock**

It is possible to select an external source, that can be used as a clock for the slope generation, HRPWMx.ECLKy. This clock is synchronized internally with the module clock and therefore the external clock needs to meet the criterion described on **Table 32**.

<sup>2)</sup> Only valid if the signal was not previously synchronized/generated with the fccu clock (or a synchronous clock)



# Table 38 Power Supply Parameters

Parameter	Symbol		Values			Unit	Note /
			Min.	Тур.	Max.		Test Condition
Power Dissipation	$P_{DISS}$	CC	_	_	1	W	$V_{\rm DDP} = 3.6 \text{ V},$ $T_{\rm J} = 150 ^{\circ}\text{C}$
Wake-up time from Sleep to Active mode	$t_{SSA}$	CC	_	6	_	cycles	
Wake-up time from Deep Sleep to Active mode			_	_	-	ms	Defined by the wake-up of the Flash module, see Section 3.2.11
Wake-up time from Hibernate mode			-	_	_	ms	Wake-up via power-on reset event, see Section 3.3.2

- 1) CPU executing code from Flash, all peripherals idle.
- 2) CPU executing code from Flash. USB and CCU clock off.
- 3) CPU in sleep, all peripherals idle, Flash in Active mode.
- 4) CPU in sleep, Flash in Active mode.
- 5) CPU in sleep, peripherals disabled, after wake-up code execution from RAM.
- 6) To wake-up the Flash from its Sleep mode,  $f_{CPII} \ge 1$  MHz is required.
- 7) OSC\_ULP operating with external crystal on RTC\_XTAL
- 8) OSC\_ULP off, Hibernate domain operating with OSC\_SI clock
- 9) Test Power Loop: f<sub>SYS</sub> = 80 MHz, CPU executing benchmark code from Flash, all CCUs in 100kHz timer mode, all ADC groups in continuous conversion mode, USICs as SPI in internal loop-back mode, CAN in 500kHz internal loop-back mode, interrupt triggered DMA block transfers to parity protected RAMs and FCE, DTS measurements and FPU calculations.
  - The power consumption of each customer application will most probably be lower than this value, but must be evaluated separately.
- 10)  $I_{\rm DDP}$  decreases typically by 3.5 mA when  $f_{\rm SYS}$  decreases by 10 MHz, at constant  $T_{\rm J}$
- 11) Sum of currents of all active converters (ADC and DAC)



# 3.2.11 Flash Memory Parameters

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 40 Flash Memory Parameters

Parameter	Symbol		Values	5	Unit	Note / Test Condition
		Min.	Тур.	Max.		
Erase Time per 256 Kbyte Sector	$t_{ERP}CC$	_	5	5.5	S	
Erase Time per 64 Kbyte Sector	t <sub>ERP</sub> CC	_	1.2	1.4	S	
Erase Time per 16 Kbyte Logical Sector	t <sub>ERP</sub> CC	_	0.3	0.4	S	
Program time per page <sup>1)</sup>	$t_{PRP}CC$	_	5.5	11	ms	
Erase suspend delay	t <sub>FL_ErSusp</sub>	_	-	15	ms	
Wait time after margin change	t <sub>FL_Margin</sub>	10	-	_	μS	
Wake-up time	$t_{WU}CC$	_	_	270	μS	
Read access time	t <sub>a</sub> CC	20	-	_	ns	For operation with $1/f_{\rm CPU} < t_{\rm a}$ wait states must be configured <sup>2)</sup>
Data Retention Time, Physical Sector <sup>3)4)</sup>	$t_{RET}CC$	20	-	-	years	Max. 1000 erase/program cycles
Data Retention Time, Logical Sector <sup>3)4)</sup>	t <sub>RETL</sub> CC	20	_	-	years	Max. 100 erase/program cycles



### 3.3 AC Parameters

# 3.3.1 Testing Waveforms

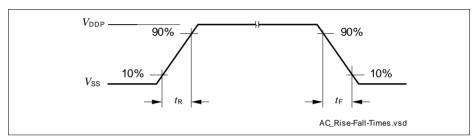


Figure 23 Rise/Fall Time Parameters

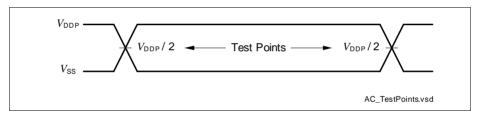


Figure 24 Testing Waveform, Output Delay

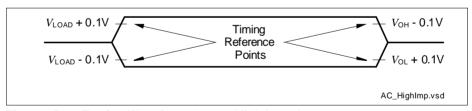


Figure 25 Testing Waveform, Output High Impedance



Table 42 Power Sequencing Parameters

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Positive Load Step Current	$\Delta I_{PLS}SR$	-	_	50	mA	Load increase on $V_{\rm DDP}$ $\Delta t \leq 10 \text{ ns}$
Negative Load Step Current	$\Delta I_{NLS}SR$	-	_	150	mA	Load decrease on $V_{\text{DDP}}$ $\Delta t \leq 10 \text{ ns}$
V <sub>DDC</sub> Voltage Over- / Undershoot from Load Step	$\Delta V_{LS}$ CC	-	_	±100	mV	For maximum positive or negative load step
Positive Load Step Settling Time	t <sub>PLSS</sub> SR	50	_	-	μS	
Negative Load Step Settling Time	t <sub>NLSS</sub> SR	100	-	-	μS	
External Buffer Capacitor on $V_{\mathrm{DDC}}$	C <sub>EXT</sub> SR	3	4.7	6	μF	In addition $C = 100 \text{ nF}$ capacitor on each $V_{\text{DDC}}$ pin

### **Positive Load Step Examples**

System assumptions:

 $f_{\rm CPU}$  =  $f_{\rm SYS}$ , target frequency  $f_{\rm CPU}$  = 80 MHz, main PLL  $f_{\rm VCO}$  = 480 MHz, stepping done by K2 divider,  $t_{\rm PLSS}$  between individual steps:

24 MHz - 48 MHz - 80 MHz (K2 steps 20 - 10 - 6)

24 MHz - 60 MHz - 80 MHz (K2 steps 20 - 8 - 6)



# 3.3.4 Phase Locked Loop (PLL) Characteristics

### Main and USB PLL

Table 43 PLL Parameters

Parameter	Symbol		Value	S	Unit	Note / Test Condition
		Min.	Тур.	Max.		
Accumulated Jitter	$D_{P}CC$	_	-	±5	ns	accumulated over 300 cycles $f_{\rm SYS}$ = 80 MHz
Duty Cycle <sup>1)</sup>	D <sub>DC</sub> CC	46	50	54	%	Low pulse to total period, assuming an ideal input clock source
PLL base frequency	$f_{ m PLLBASE}$ CC	30	_	140	MHz	
VCO input frequency	$f_{REF}CC$	4	_	16	MHz	
VCO frequency range	$f_{\sf VCO}\sf CC$	260	_	520	MHz	
PLL lock-in time	$t_{L}$ CC	_	_	400	μS	

<sup>1) 50%</sup> for even K2 divider values, 50±(10/K2) for odd K2 divider values.



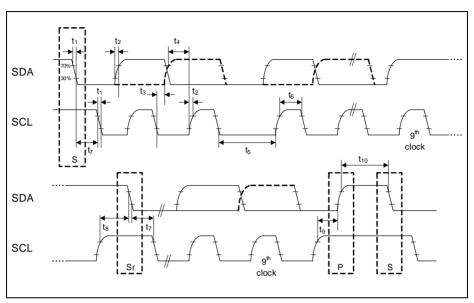


Figure 32 USIC IIC Stand and Fast Mode Timing

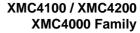
# 3.3.8.3 Inter-IC Sound (IIS) Interface Timing

The following parameters are applicable for a USIC channel operated in IIS mode.

Note: Operating Conditions apply.

Table 52 USIC IIS Master Transmitter Timing

Parameter	Symbol		Values	3	Unit	Note / Test Condition
		Min.	Тур.	Max.		
Clock period	t <sub>1</sub> CC	33.3	-	_	ns	
Clock high time	t <sub>2</sub> CC	0.35 x	_	_	ns	
		$t_{1min}$				
Clock low time	t <sub>3</sub> CC	0.35 x	_	_	ns	
		$t_{1min}$				
Hold time	t <sub>4</sub> CC	0	_	_	ns	
Clock rise time	t <sub>5</sub> CC	-	_	0.15 x	ns	
				$t_{1min}$		





#### Package and Reliability

power dissipation must be limited so that the average junction temperature does not exceed 150 °C.

The difference between junction temperature and ambient temperature is determined by  $\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta,IA}$ 

The internal power consumption is defined as

 $P_{\text{INT}} = V_{\text{DDP}} \times I_{\text{DDP}}$  (switching current and leakage current).

The static external power consumption caused by the output drivers is defined as  $P_{\text{IOSTAT}} = \Sigma((V_{\text{DDP}} - V_{\text{OH}}) \times I_{\text{OH}}) + \Sigma(V_{\text{OL}} \times I_{\text{OL}})$ 

The dynamic external power consumption caused by the output drivers ( $P_{\mathsf{IODYN}}$ ) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

- Reduce  $V_{\rm DDP}$ , if possible in the system
- · Reduce the system frequency
- Reduce the number of output pins
- · Reduce the load on active output drivers